

**DESCRIPTION**

The MGF4934CM super-low noise HEMT (High Electron Mobility Transistor) is designed for use in S to Ku band amplifiers.

The 4pin flat lead package is small-thin size, and offers high cost performance.

**FEATURES**

Low noise figure @ f=12GHz  
NFmin. = 0.50dB (Typ.)

High associated gain @ f=12GHz  
Gs = 13.0dB (Typ.)

**APPLICATION**

S to Ku band low noise amplifiers

**QUALITY GRADE**

GG

**RECOMMENDED BIAS CONDITIONS**

$V_{DS}=2V$ ,  $I_D=10mA$

**ORDERING INFORMATION**

Tape & reel 3000pcs/reel

**Outline Drawing**

Fig.1

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**ABSOLUTE MAXIMUM RATINGS**

(Ta=25°C)

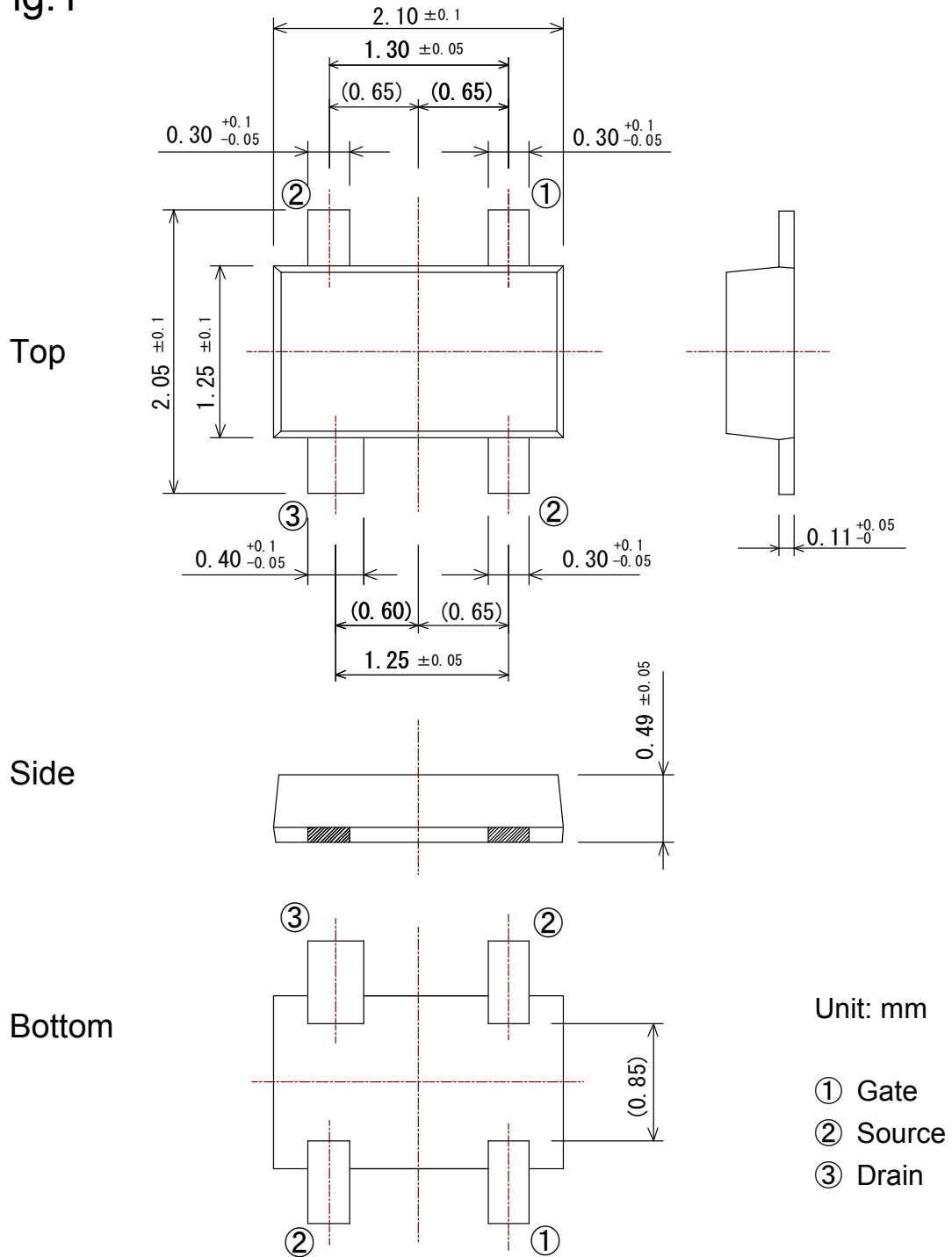
Symbol	Parameter	Ratings	Unit
$V_{GDO}$	Gate to drain voltage	-3	V
$V_{GSO}$	Gate to source voltage	-3	V
$I_D$	Drain current	IDSS	mA
PT	Total power dissipation	50	mW
$T_{ch}$	Channel temperature	125	°C
$T_{stg}$	Storage temperature	-55 to +125	°C

**ELECTRICAL CHARACTERISTICS**

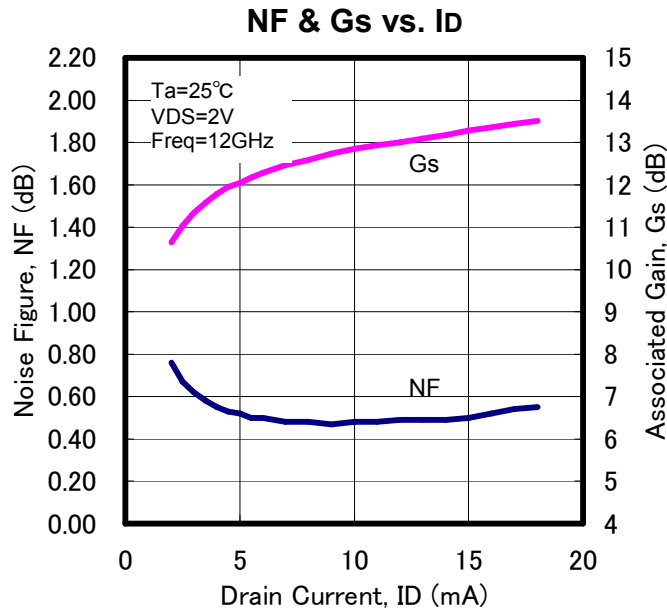
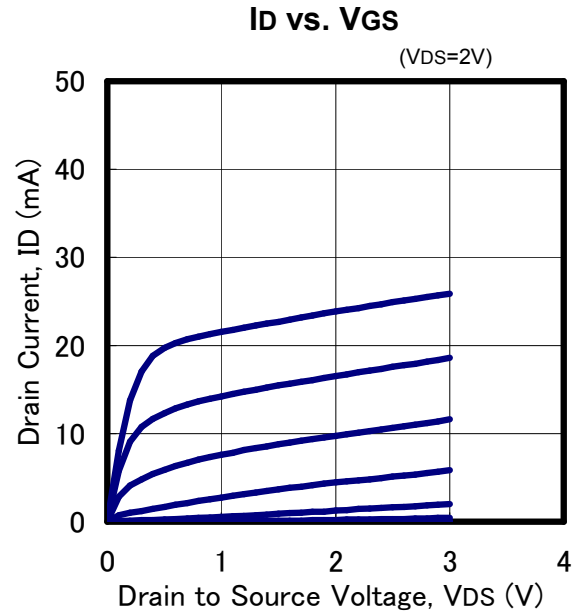
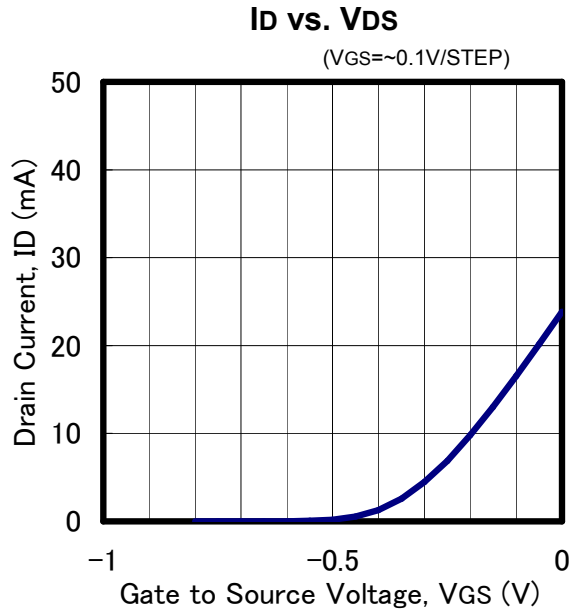
(Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			MIN.	TYP.	MAX	
$V_{(BR)GDO}$	Gate to drain breakdown voltage	$I_G=-10\mu A$	-3.5	--	--	V
$I_{GSS}$	Gate to source leakage current	$V_{GS}=-2V, V_{DS}=0V$	--	--	50	$\mu A$
$I_{DSS}$	Saturated drain current	$V_{GS}=0V, V_{DS}=2V$	12	--	60	mA
$V_{GS(off)}$	Gate to source cut-off voltage	$V_{DS}=2V, I_D=500\mu A$	-0.1	--	-1.5	V
Gs	Associated gain	$V_{DS}=2V,$	11.5	13.0	--	dB
NFmin.	Minimum noise figure	$I_D=10mA, f=12GHz$	--	0.50	0.75	dB

Fig.1



TYPICAL CHARACTERISTICS (Ta=25°C)



## S PARAMETERS

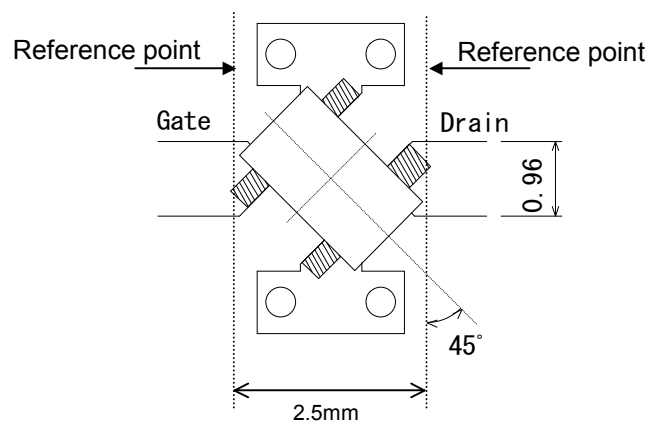
(V<sub>DS</sub>=2V, I<sub>D</sub>=10mA, T<sub>a</sub>=room temperature)

Freq. (GHz)	S11		S21		S12		S22	
	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)	(mag)	(ang)
1	0.990	-16.3	5.156	158.7	0.032	79.5	0.758	-9.2
2	0.985	-30.1	4.971	145.3	0.037	70.2	0.728	-19.5
3	0.930	-43.8	4.787	131.9	0.042	60.9	0.698	-29.9
4	0.860	-57.5	4.602	118.5	0.047	51.6	0.668	-40.3
5	0.802	-72.1	4.470	103.9	0.055	43.4	0.634	-50.0
6	0.737	-87.3	4.343	89.3	0.061	36.2	0.594	-59.5
7	0.668	-103.2	4.212	74.6	0.066	29.7	0.555	-68.9
8	0.599	-119.6	4.042	60.2	0.070	24.0	0.514	-78.3
9	0.533	-136.5	3.852	46.4	0.072	18.9	0.473	-87.3
10	0.477	-152.0	3.672	33.9	0.072	17.3	0.440	-95.2
11	0.442	-168.0	3.537	21.6	0.076	17.1	0.418	-104.2
12	0.421	175.7	3.429	9.5	0.083	17.2	0.400	-114.1
13	0.406	159.0	3.331	-2.4	0.090	15.9	0.383	-124.4
14	0.405	142.8	3.264	-14.1	0.099	14.1	0.375	-135.6
15	0.425	126.5	3.236	-26.9	0.115	10.1	0.379	-150.3
16	0.460	110.8	3.214	-40.8	0.137	5.3	0.403	-168.9
17	0.503	94.9	3.149	-54.5	0.156	-2.2	0.417	172.6
18	0.547	80.2	3.058	-68.3	0.175	-11.2	0.448	153.5

## Noise Parameter

(V<sub>DS</sub>=2V, I<sub>D</sub>=10mA, T<sub>a</sub>=room temperature)

Freq. (GHz)	NFmin (dB)	Γ <sub>opt</sub>		R <sub>n</sub> (Ω)
		(mag)	(ang)	
1	0.25	0.97	8.2	17.5
2	0.25	0.97	14.5	15.4
3	0.26	0.94	22.9	14.0
4	0.29	0.91	30.2	12.5
5	0.30	0.88	40.2	11.0
6	0.32	0.82	48.2	9.5
7	0.35	0.74	61.2	8.0
8	0.37	0.65	75.5	6.5
9	0.39	0.57	91.3	5.0
10	0.42	0.49	108.4	3.6
11	0.46	0.44	127.0	2.6
12	0.49	0.39	146.9	1.9
13	0.53	0.34	168.2	1.8
14	0.57	0.30	-169.1	2.0

Board: ε<sub>r</sub>=2.6

Thickness: 0.4mm

(4-φ0.4: through-hole)

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